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TITLE: REMOVAL OF RESIST RESIDUE
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INVENTOR-INFORMATION:
NAME
SUGANO, ITARU

ASSIGNEE-INFORMATION:
NAME MITSUBISHI ELECTRIC CORP
COUNTRY N/A

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ABSTRACT:

PURPOSE: To enable removal of resist residues without corrosion of wiring films by washing with pure water mixed with an oxidizer after washing with an organic solvent and an acid alkaline chemical and then by drying.

CONSTITUTION: A semiconductor substrate is overlaid with an insulating film 8, and a contact hole 10 reaching a wiring film 6 on an insulating film 5 is formed. At this time, for removal of produced resist residues, washing is conducted with pure water mixed with an oxidizer such as oxygen gas or ozone gas after washing with an organic solvent and an acid alkaline chemical. This process causes the wiring film 6 to be surfaced with an aluminum oxide film 17 upon contact with water, which film suppresses corrosion of the wiring film. Washing in a dark free of light under a low temperature of 0-10°C further reduces corrosion reaction.

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